

P-Channel 12-V (D-S) MOSFET

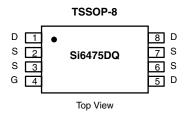
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 12	0.011 at V _{GS} = - 4.5 V	- 10		
	0.0135 at V _{GS} = - 2.5 V	- 9		
	0.017 at V _{GS} = - 1.8 V	- 8		

FEATURES

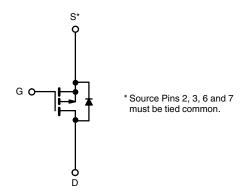
- Halogen-free
- TrenchFET® Power MOSFETs



RoHS COMPLIANT



Ordering Information: Si6475DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise r	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V_{DS}	- 12		V	
Gate-Source Voltage		V_{GS}	± 8			
Continuous Drain Current /T 150 °C\2	T _A = 25 °C	- I _D	- 10	- 7.8	۸	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 8	- 6.2		
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	- 30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.5	- 0.95		
M	T _A = 25 °C	P _D	1.75	1.08	W	
Maximum Power Dissipation ^a	T _A = 70 °C		1.14	0.69		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifesture Installant to Austriant	t ≤ 10 s	R _{thJA}	55	70	°C/W
Maximum Junction-to-Ambient ^a	Steady State		95	115	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	35	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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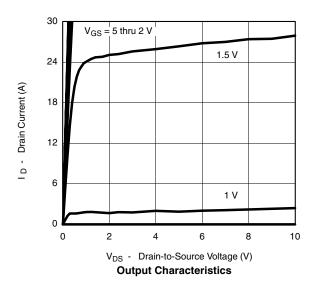
SPECIFICATIONS $T_J = 25$ °C	C, unless o	otherwise noted					
Parameter	Symbol	Test Conditions	Test Conditions Min.		Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -5 \text{ mA}$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 9.6 V, V _{GS} = 0 V			- 1	μΑ	
		V _{DS} = - 9.6 V, V _{GS} = 0 V, T _J = 70 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	20			Α	
		V _{GS} = - 4.5 V, I _D = - 10 A		0.009	0.011		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 9 A		0.011	0.0135	Ω	
		V _{GS} = - 1.8 V, I _D = - 8 A		0.014	0.017	Ī	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10 A		50		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.5 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.68	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			49.5	70		
Gate-Source Charge	Q_{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -10 \text{ A}$		7.7		nC	
Gate-Drain Charge	Q_{gd}			8.5		1	
Turn-On Delay Time	t _{d(on)}			56	85		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		62	100		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		300	450	ns	
Fall Time	t _f			185	270		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.5 A, dl/dt = 100 A/μs		90	150		

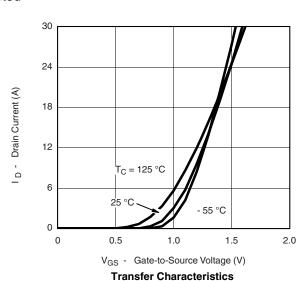
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

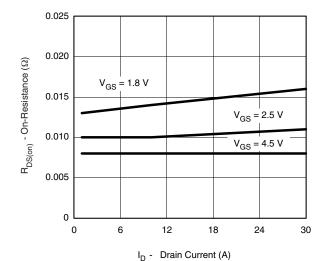




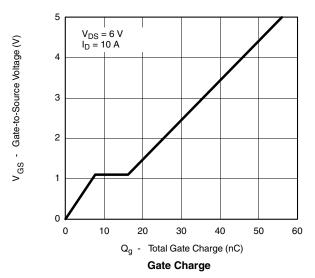


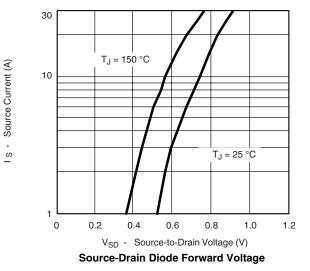


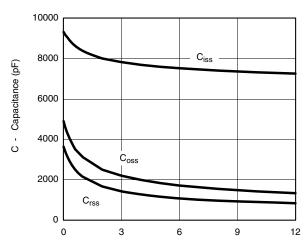
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On-Resistance vs. Drain Current

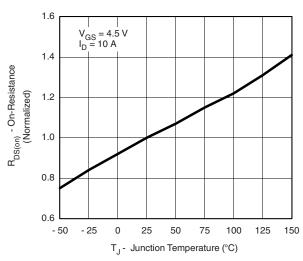




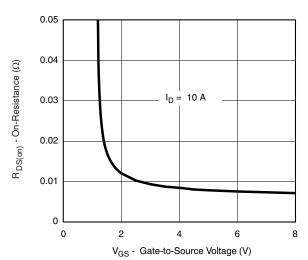


V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

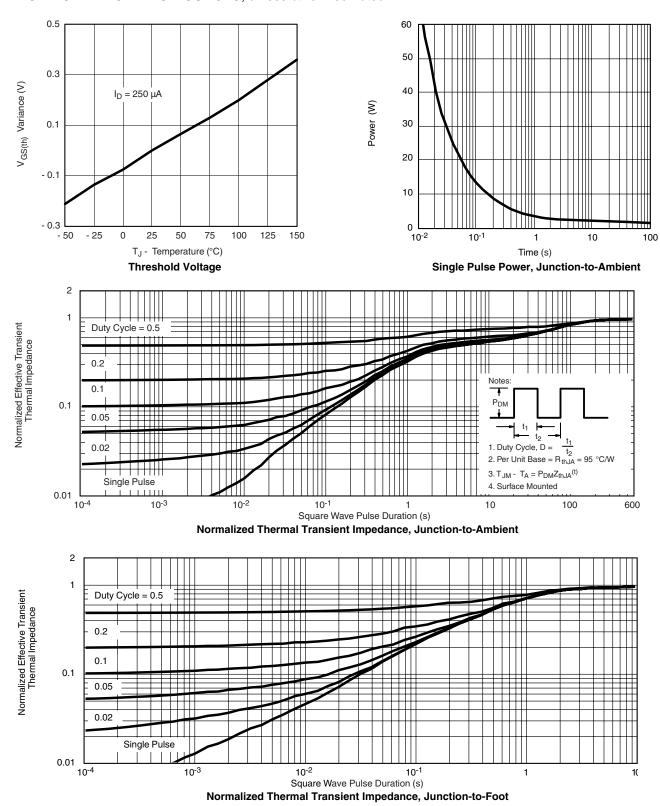


On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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